SEMICONDUCTOR®

74VHC04 Hex Inverter

General Description

The VHC04 is an advanced high speed CMOS Inverter fabricated with silicon gate CMOS technology. It achieves the high speed operation similar to equivalent Bipolar Schottky TTL while maintaining the CMOS low power dissipation.

The internal circuit is composed of 3 stages including buffer output, which provide high noise immunity and stable output. An input protection circuit ensures that 0V to 7V can be applied to the input pins without regard to the supply voltage. This device can be used to interface 5V to 3V systems and two supply systems such as battery back up. This circuit prevents device destruction due to mismatched supply and input voltages.

November 1992

Revised February 2005

Features

- High Speed: t_{PD} = 3.8 ns (typ) at V_{CC} = 5V
- \blacksquare High noise immunity: V_{NIH} = V_{NIL} = 28% V_{CC} (Min)
- Power down protection is provided on all inputs
- Low Noise: V_{OLP} = 0.4V (typ)
- \blacksquare Low power dissipation: I_{CC} = 2 μA (Max) @ T_A = 25°C
- Pin and function compatible with 74HC04

Ordering Code:

Order Number	Package Number	Package Description
74VHC04M	M14A	14-Lead Small Outline Integrated Circuit (SOIC), JEDEC MS-012, 0.150" Narrow
74VHC04MX_NL (Note 1)	M14A	Pb-Free 14-Lead Small Outline Integrated Circuit (SOIC), JEDEC MS-012, 0.150" Narrow
74VHC04SJ	M14D	Pb-Free 14-Lead Small Outline Package (SOP), EIAJ TYPE II, 5.3mm Wide
74VHC04MTC	MTC14	14-Lead Thin Shrink Small Outline Package (TSSOP), JEDEC MO-153, 4.4mm Wide
74VHC04MTCX_NL (Note 1)	MTC14	Pb-Free 14-Lead Thin Shrink Small Outline Package (TSSOP), JEDEC MO-153, 4.4mm Wide
74VHC04N	N14A	14-Lead Plastic Dual-In-Line Package (PDIP), JEDEC MS-001, 0.300" Wide

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Description

Inputs

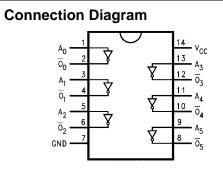
Outputs

Pin Descriptions

 A_n

 \overline{O}_n

Pin Names



Truth Table

Α	ō
L	Н
Н	L

Absolute Maximum Ratings(Note 2)

Supply Voltage (V _{CC})	-0.5V to +7.0V
DC Input Voltage (V _{IN})	-0.5V to +7.0V
DC Output Voltage (V _{OUT})	–0.5V to V _{CC} + 0.5V
Input Diode Current (I _{IK})	–20 mA
Output Diode Current (I _{OK})	±20 mA
DC Output Current (I _{OUT})	±25 mA
DC V _{CC} /GND Current (I _{CC})	±50 mA
Storage Temperature (T _{STG})	–65°C to +150°C
Lead Temperature (T _L)	
(Soldering, 10 seconds)	260°C

Recommended Operating

Conditions (Note 3)

Supply Voltage (V _{CC})	2.0V to +5.5V
Input Voltage (V _{IN})	0V to +5.5V
Output Voltage (V _{OUT})	0V to V _{CC}
Operating Temperature (T _{OPR})	-40°C to +85°C
Input Rise and Fall Time (t_r, t_f)	
$V_{CC} = 3.3V \pm 0.3V$	0 ~ 100 ns/V
$V_{CC} = 5.0V \pm 0.5V$	0 ~ 20 ns/V

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Note 2: Absolute Maximum Ratings are values beyond which the device may be damaged or have its useful life impaired. The databook specifications should be met, without exception, to ensure that the system design is reliable over its power supply, temperature, and output/input loading variables. Fairchild does not recommend operation outside databook specifications.

Note 3: Unused inputs must be held HIGH or LOW. They may not float.

DC Electrical Characteristics

Symbol	Parameter	V _{CC}	$T_A = 25^{\circ}C$			$\textbf{T}_{\textbf{A}}=-40^{\circ}\textbf{C} \text{ to }+85^{\circ}\textbf{C}$		Units	Conditions	
		(V)	Min	Тур	Max	Min	Max	Units	Conditions	
V _{IH}	HIGH Level	2.0	1.50			1.50		V		
	Input Voltage	3.0 – 5.5	0.7 V _{CC}			0.7 V _{CC}		v		
V _{IL}	LOW Level	2.0			0.50		0.50	V		
	Input Voltage	3.0 - 5.5			0.3 V _{CC}		0.3 V _{CC}			
V _{OH}	HIGH Level	2.0	1.9	2.0		1.9			$V_{IN} = V_{IH}$ $I_{OH} = -50 \ \mu A$	
	Output Voltage	3.0	2.9	3.0		2.9		V	or V _{IL}	
		4.5	4.4	4.5		4.4				
		3.0	2.58			2.48		V	I _{OH} = -4 mA	
		4.5	3.94			3.80		v	$I_{OH} = -8 \text{ mA}$	
V _{OL}	LOW Level	2.0		0.0	0.1		0.1		$V_{IN} = V_{IH} I_{OL} = +50 \ \mu A$	
	Output Voltage	3.0		0.0	0.1		0.1	V	or V _{IL}	
		4.5		0.0	0.1		0.1			
		3.0			0.36		0.44	V	I _{OL} = 4 mA	
		4.5			0.36		0.44	v	I _{OL} = 8 mA	
I _{IN}	Input Leakage Current	0 - 5.5			±0.1	1	±1.0	μA	$V_{IN} = 5.5V$ or GND	
I _{CC}	Quiescent Supply Current	5.5			2.0		20.0	μA	V _{IN} = V _{CC} or GND	

Noise Characteristics

Symbol	Parameter	v _{cc} (V)	T _A = 25°C		Units	Conditions	
Cymbol			Тур	Limits	onno	Contanions	
V _{OLP} (Note 4)	Quiet Output Maximum Dynamic V _{OL}	5.0	0.4	0.8	V	C _L = 50 pF	
V _{OLV} (Note 4)	Quiet Output Minimum Dynamic V _{OL}	5.0	-0.4	-0.8	V	C _L = 50 pF	
V _{IHD} (Note 4)	Minimum HIGH Level Dynamic Input Voltage	5.0		3.5	V	C _L = 50 pF	
V _{ILD} (Note 4)	Maximum LOW Level Dynamic Input Voltage	5.0		1.5	V	C _L = 50 pF	

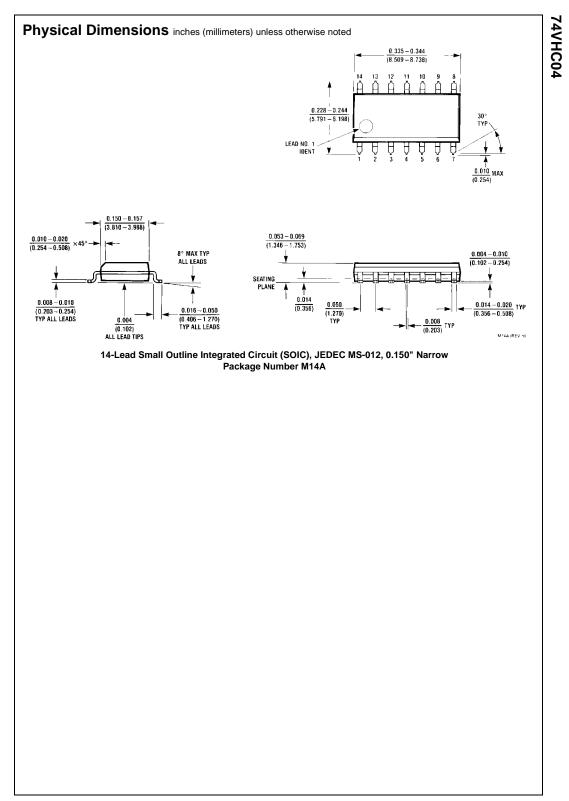
Note 4: Parameter guaranteed by design.

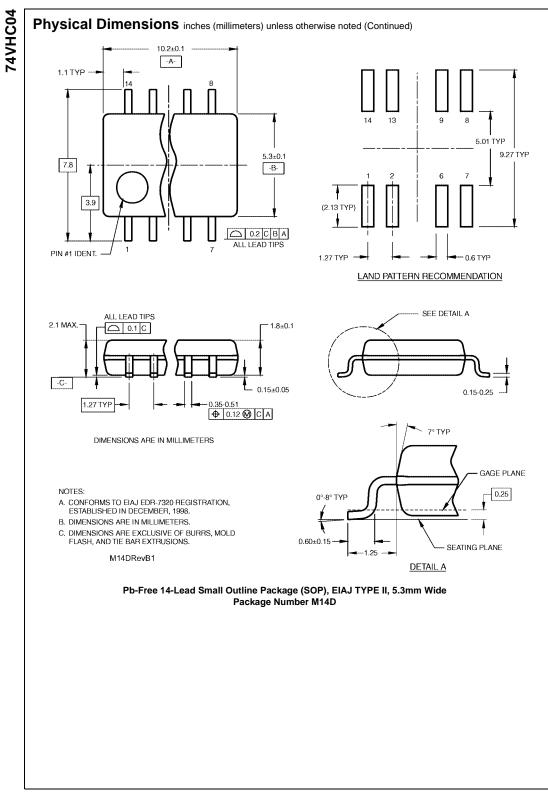


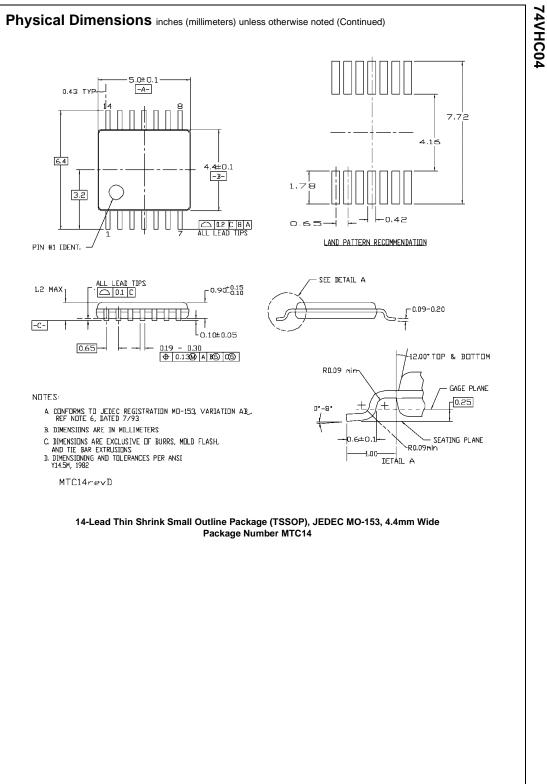
AC Electrical Characteristics

Symbol	Parameter	V _{CC} (V)		$T_A = 25^{\circ}C$		$T_A = -40^{\circ}C \text{ to } +85^{\circ}C$		Units	Conditions
			Min	Тур	Max	Min	Max	Units	Conditions
PHL	Propagation Delay	$\textbf{3.3}\pm\textbf{0.3}$		5.0	7.1	1.0	8.5	ns	C _L = 15 pF
t _{PLH}		-		7.5	10.6	1.0	12.0		$C_L = 50 \text{ pF}$
		5.0 ± 0.5		3.8	5.5	1.0	6.5	ns	C _L = 15 pF
		-		5.3	7.5	1.0	8.5		$C_L = 50 \text{ pF}$
2 _{IN}	Input Capacitance			4	10		10	pF	$V_{CC} = OPEN$
C _{PD}	Power Dissipation Capacitance			18				pF	(Note 5)

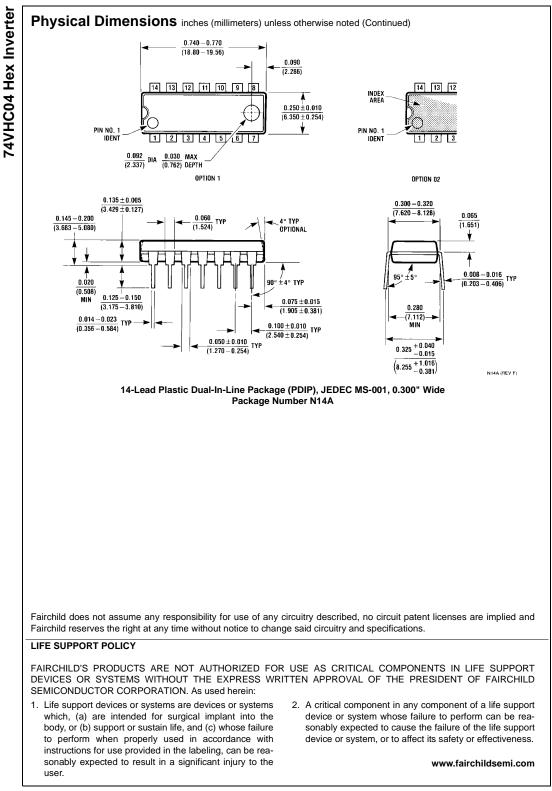
operating current can be obtained by the equation: I_{CC} (opr.) = $C_{PD} * V_{CC} * f_{IN} + I_{CC}/6$ (per gate).







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